

MXD8621EC

SPDT Switch for 0.1~6.0GHz Application





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General Description

The MXD8621EC is a Single-Pole, Double-Throw (SPDT) for 0.1~6.0GHz application. Switching is controlled by an integrated GPIO interface with a single control pin.

No external DC blocking capacitors are required as long as no DC voltage is applied on any RF path.

The MXD8621EC is provided in a compact 1.1mm x 0.7mm x 0.377mm 6-lead DFN package that meets requirements for board-level assembly.

A functional block diagram and the pin configuration are shown in Figure 1.

Applications

- GSM/WCDMA/LTE Receive
- WLAN TRX

Features

- Broadband frequency range: 0.1 to 6.0 GHz
- Low insertion loss: 0.33 dB @ 2.7 GHz

0.55 dB @ 6.0 GHz

- High isolation: 38dB @ 2.7 GHz
 30dB @ 6.0 GHz
- P0.1dB 29dBm
- No external DC blocking capacitors required
- Single GPIO control line with VDD voltage regulator:

 $V_{DD} = 1.62 \text{ to } 3.60 \text{ V}$

 Small, 6-Lead DFN, 400 um pitch (1.1mm x 0.7mmx 0.377 mm) package , MSL1

Functional Block Diagram and Pin Function

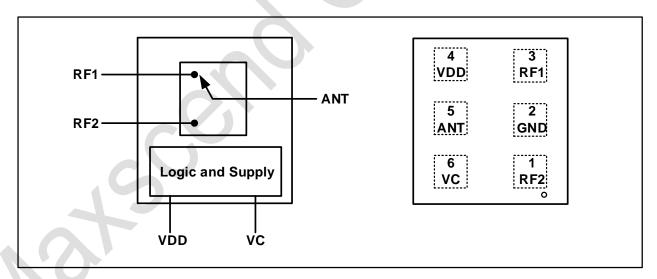


Figure 1 Functional Block Diagram and Pin-out (Top View)



Application Circuit

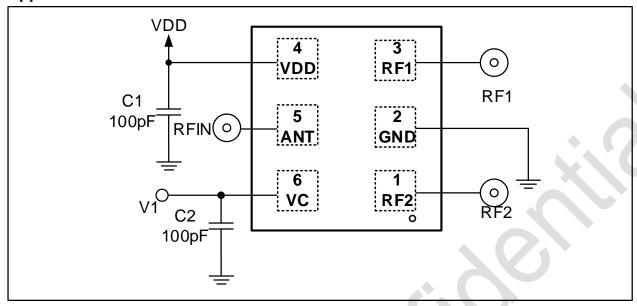


Figure 2 MXD8621EC Application Circuit

Table 1. Pin Description

Pin No.	Name	Description	Pin No.	Name	Description	
1	RF2	RF I/O. Throw 1 of the switch.	6	VC	Logic Control	
2	GND	Ground	5	ANT	Antenna	
3	RF1	RF I/O. Throw 2 of the switch.	4	VDD	Supply	

Truth Table

Table 2.

State	Active Path	VC
0	ANT to RF1	0
1	ANT to RF2	1

Note: "1" = 1.2 V to V_{DD} V. "0" = 0 V to +0.3 V.

Recommended Operation Range

Table 3.

Parameters	Symbol	Min	Тур	Max	Units
Operation Frequency	f1	0.1		6.0	GHz
Power supply	V_{DD}	1.62	1.8	3.60	V
Switch Control Voltage High	V _{CTL_} H	1.2	1.8	V_{DD}	V
Switch Control Voltage Low	V _{CTL_L}	0	0	0.3	V



Specifications

Table 4.Electrical Specifications

Danamatan	O	Specification		I limit a	Took Condition		
Parameter	Symbol	Min.	Typical	Max.	Units	Test Condition	
DC Specifications					1		
Supply voltage	V_{DD}	1.62	1.8	3.60	V		
Control voltage: Low High	V _{CTL_L} V _{CTL_H}	0 1.2	0 1.8	0.3 V _{DD}	V	+ 0	
Current on VC pin	ICTL			5	μA		
Supply current	I _{DD}		100	140	μA	V _{DD} = 1.8 V	
DC supply turn- on/turn-off time	ton			10	μs	Measured from 50% of final V _{DD} supply voltage to 90% of final RF power	
RF path switching time	tsw		130	200	ns	From one active state to another active state transition, measured from 50% of final control voltage to 90% of final RF power	
Supply ripple	V_{PP}			50	mV_{pp}		
			RF Speci	fications			
			0.28	0.35	dB	700 to 960 MHz	
Insertion loss (RF1 or RF2 to ANT pin)	IL		0.30 0.33 0.40 0.55	0.40 0.45 0.50 0.65	dB dB dB dB	1710 to 2170 MHz 2170 to 2690 MHz 3600 to 3800 MHz 4800 to 6000 MHz	
Isolation (ANT to RF1 or RF2)	ISO	50 42 35 31 27	56 45 38 34 30		dB dB dB dB	700 to 960 MHz 1710 to 2170 MHz 2170 to 2690 MHz 3600 to 3800 MHz 4800 to 6000 MHz	
Isolation (RF1 to RF2)	ISO	49 41 34 30 26	55 44 37 33 29		dB dB dB dB	700 to 960 MHz 1710 to 2170 MHz 2170 to 2690 MHz 3600 to 3800 MHz 4800 to 6000 MHz	
Input return loss (ANT to RF1 or RF2)	RL	13	20		dB	700 to 6000 MHz	
Voltage Standing Wave Ratio, all ports	VSWR		1.25:1	1.5:1	-	Referenced to 50 Ω, 700 to 6000 MHz	
0.1dB compression							
point (from antenna		29			dBm	700M to 6000MHz	
to RF1 and RF2)						25% duty pulse	
2nd Harmonic (ANT to RF1 or RF2)	2fo		-62	-55	dBm	fo _ 050 MHz DIN _ 126 dD	
3rd Harmonic (ANT to RF1 or RF2)	3fo		-62	-55	dBm	fo = 950 MHz, PIN = +26 dBm	
2nd Intermodulation Distortion	IMD2		-103	-100	dBm	Two-tone test : f0=24dBm and f1= -	
3rd Intermodulation Distortion	IMD3		-103	-100	dBm	15dBm at f0+1MHz	



Absolute Maximum Ratings

Table 5. Maximum ratings

Parameters	Symbol	Minimum	Maximum	Units
Supply voltage	V _{DD}	+1.62	+3.7	V
Digital control voltage	Vctl	0	+3.7	V
RF input power	P _{IN}		+30	dBm
Operating temperature	Top	-40	+85	°C
Storage temperature	T _{STG}	-55	+150	°C
Humidity Grade		MSL1		. (7
Storage Cycle(package)		2		years
Electrostatic Discharge Human body model (HBM), Class 1C	ESD_HBM		1000	
Machine Model (MM), Class A	ESD_MM		100	V
Charged device model (CDM), Class III	ESD_CDM		500	

Note: Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.



Package Outline Dimension

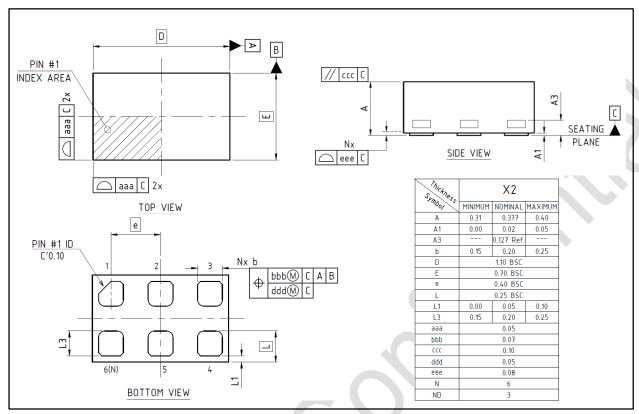


Figure 3. Package outline dimension



Marking Specification

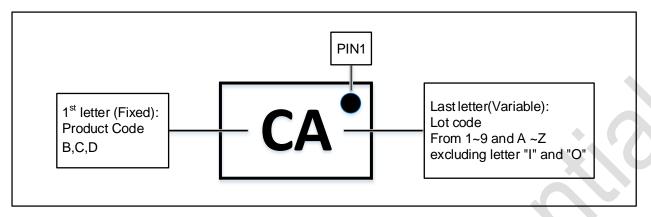


Figure 4 Marking specification (Top View)

Tape and Reel Dimensions

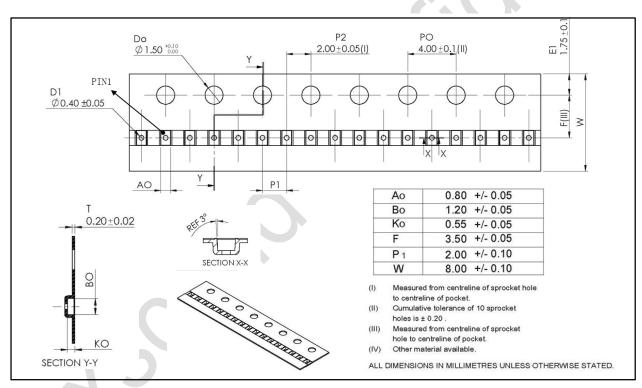


Figure 5 Tape and reel dimensions

Minimum packing Quantity

The minimum packing quantity of this device is 10000.



Reflow Chart

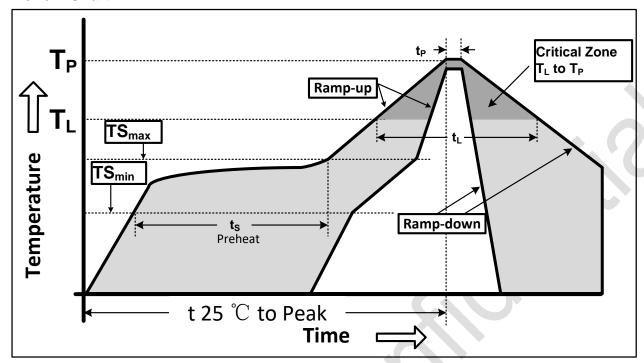


Figure 6. Recommended Lead-Free Reflow Profile

Table 6.

Profile Parameter	Lead-Free Assembly, Convection, IR/Convection		
Ramp-up rate (TS _{max} to T _p)	3°C/second max.		
Preheat temperature (TS _{min} to TS _{max})	150°C to 200°C		
Preheat time (t _s)	60 - 180 seconds		
Time above TL , 217°C (t _L)	60 - 150 seconds		
Peak temperature (T _p)	260℃		
Time within 5°C of peak temperature(t _p)	20 - 40 seconds		
Ramp-down rate	6°C/second max.		
Time 25℃ to peak temperature	8 minutes max.		

ESD Sensitivity

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be used when handling these devices.

RoHS Compliant

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.